NPN Epitaxial Planar Silicon Transistor



15C02SS

Low-Frequency General-Purpose Amplifier Applications

Applications

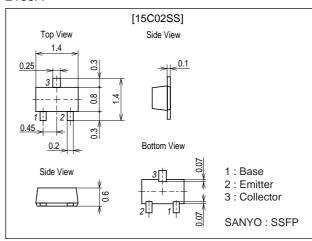
• Low-frequency amplifer, high-speed switching, small motor drive.

Features

- Large current capacitance.
- Low collector-to-emitter saturation voltage (resistance). RCE(sat) typ= $300m\Omega[IC=1A, IB=50mA]$.
- Ultrasmall package facilitates miniaturization in end products.
- Small ON-resistance (Ron).

Package Dimensions

unit : mm 2159A



Specifications

Absolute Maximum Ratings at Ta=25°C

| Parameter | Symbol | Conditions | Ratings | Unit |
|------------------------------|--------|--|-------------|------|
| Collector-to-Base Voltage | VCBO | | 20 | V |
| Collector-to-Emitter Voltage | VCEO | | 15 | V |
| Emitter-to-Base Voltage | VEBO | | 5 | V |
| Collector Current | IC | | 0.8 | А |
| Collector Current (Pulse) | ICP | | 1.6 | А |
| Collector Dissipation | PC | Mounted on a glass epoxy board (20×30×1.6mm) | 200 | mW |
| Junction Temperature | Tj | | 150 | °C |
| Storage Temperature | Tstg | | -55 to +150 | °C |

Electrical Characteristics at Ta=25°C

| Parameter | Symbol | Conditions | Ratings | | | Unit |
|---|-----------------------|---|---------|-----|-------------|-----------|
| | | | min | typ | max | Unit |
| Collector Cutoff Current | ICBO | V _{CB} =12V, I _E =0 | | | 100 | nA |
| Emitter Cutoff Current | IEBO | VEB=4V, IC=0 | | | 100 | nA |
| DC Current Gain | hFE | V _{CE} =2V, I _C =50mA | 300 | | 800 | |
| Gain-Bandwidth Product | fT | V _{CE} =2V, I _C =50mA | | 440 | | MHz |
| Output Capacitance | Cob | V _{CB} =10V, f=1MHz | | 4 | | pF |
| Collector-to-Emitter Saturation Voltage | V _{CE} (sat) | IC=400mA, IB=20mA | | 140 | 280 | mV |
| Base-to-Emitter Saturation Voltage | V _{BE} (sat) | IC=400mA, IB=20mA | | 0.9 | 1.2 | V |
| Jarking · VK | | | | C | ontinued on | nont noor |

Marking : YK

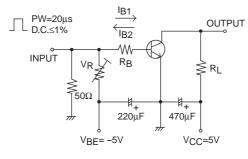
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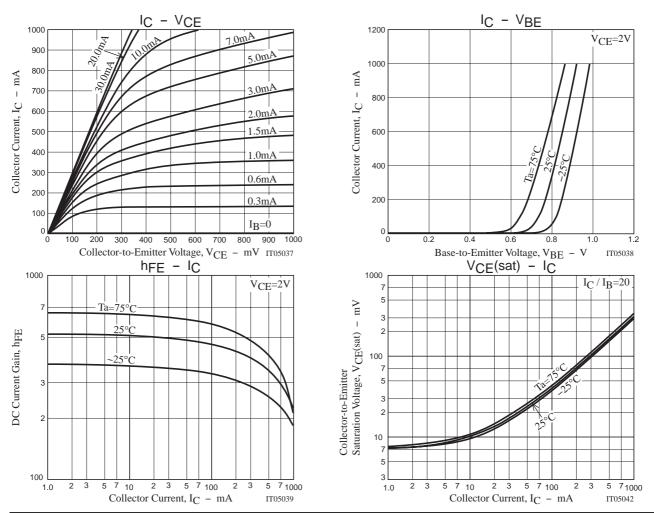
SANYO Electric Co., Ltd. Semiconductor Company TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN Continued from preceding page.

| Parameter | Symbol | Conditions | Ratings | | | Unit |
|--|----------|-----------------------------|---------|-----|-----|------|
| | | | min | typ | max | Unit |
| Collector-to-Base Breakdown Voltage | V(BR)CBO | IC=10μA, IE=0 | 20 | | | V |
| Collector-to-Emitter Breakdown Voltage | V(BR)CEO | IC=1mA, R _{BE} =∞ | 15 | | | V |
| Emitter-to-Base Breakdown Voltage | V(BR)EBO | IE=10μA, IC=0 | 5 | | | V |
| Turn-ON Delay Time | ton | See specified Test Circuit. | | 30 | | ns |
| Storage Time | tstg | See specified Test Circuit. | | 165 | | ns |
| Turn-OFF Delay Time | tf | See specified Test Circuit. | | 25 | | ns |

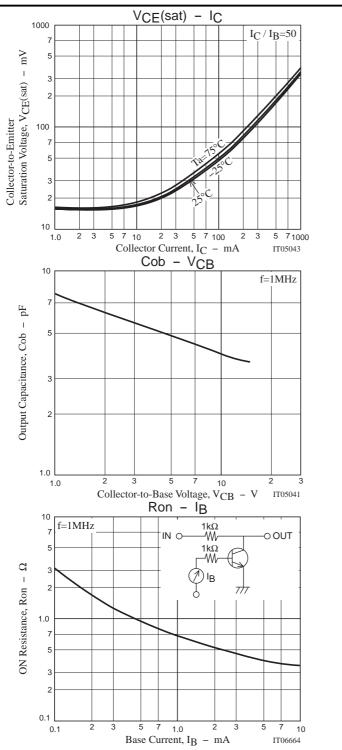
Switching Time Test Circuit

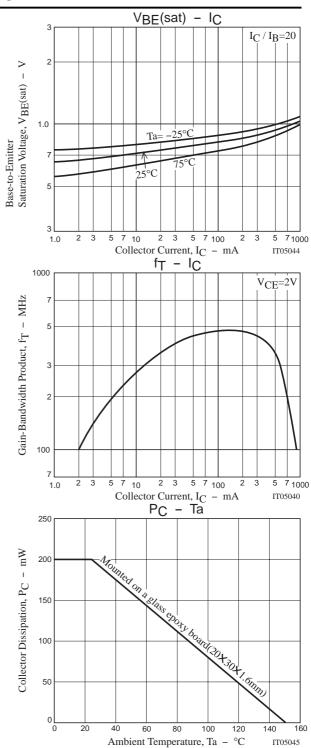


 $I_{C}=20I_{B1}=-20I_{B2}=400mA$



No.7357-2/4





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